

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27161	Application No. 10/605,672
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Bruce B. DORIS <i>et al.</i>			
			Filing Date October 16, 2003	Group 2812	

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER	<i>Shanell Isaac</i>
DATE CONSIDERED	
<i>6/23/06</i>	
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